RS3AAF THRU RS3MAF FAST RECOVERY RECTIFIERS

Features

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Easy to pick and place
- Fast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directives

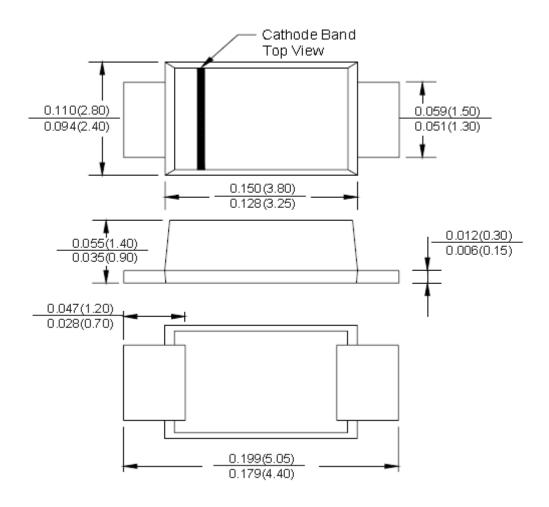
Mechanical Data

Case: SMAF

Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 27mg / 0.00095oz

Mechanical Dimensions (In Inches/mm)



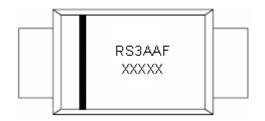
SMAF

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Marking Diagram:



Where XXXXX is YYWWL

 RS3AAF
 = Part Name

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package			
RS3AAF THRU RS3MAF	SMAF	5000pcs / reel		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.



Maximum Ratings and Electrical characteristics

Ratings at 25 $^{\circ}\text{C}$ ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	RS3AAF	RS3BAF	RS3DAF	RS3GAF	RS3JAF	RS3KAF	RS3MAF	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T _L = 100 °C	I _{F(AV)}	v) 3						Α	
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	80						Α		
Maximum Instantaneous Forward Voltage at 3 A	V _F	1.3							V
Maximum DC Reverse Current Ta = 25 °C at Rated DC Blocking Voltage Ta = 125 °C	I _R	5 150							μА
Maximum Reverse Recovery Time 1)	t _{rr}	160							ns
Typical Junction Capacitance ²⁾	Cj	60							pF
Typical Thermal Resistance ³⁾	Reja	60							°C/W
Operating and Storage Temperature Range	T _j , T _{stg} -55 ~ +150					°C			

^{1)} Measured with IF= 0.5 A, IR= 1 A, Irr= 0.25 A

²⁾ Measured at 1MHz and applied reverse voltage of 4V D.C

^{3)} P.C.B. mounted with 0.5 X 0.5" (12.7 X 12.7 mm) copper pad areas.

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Fig.1 Forward Current Derating Curve

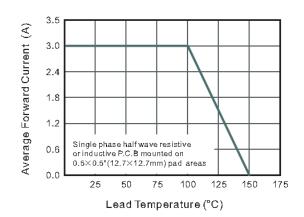


Fig.2 Typical Reverse Characteristics

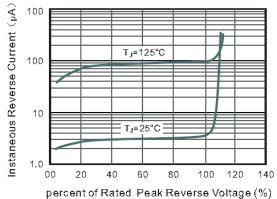


Fig.3 Typical Instaneous Forward Characteristics

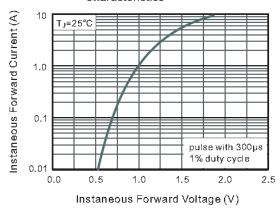


Fig.4 Typical Junction Capacitance

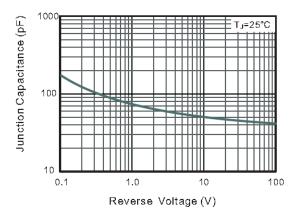
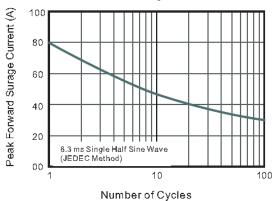


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current



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